MMBD3004SE

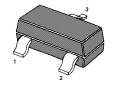
SILICON EPITAXIAL PLANAR DIODE

High Voltage Switching Diode

Features

- Fast switching speed
- High Conductance
- High Reverse Breakdown Voltage Rating





Marking Code: "ZB" SOT-23 Plastic Package

Absolute Maximum Ratings (T_a = 25 °C)

Parameter		Symbol	Value	Unit
Repetitive Peak Reverse Voltage		V_{RRM}	350	V
Working Peak Reverse Voltage		V_{RWM}	300	V
DC Blocking Voltage		V_R	300	V
Continuous Forward Current		I _F	225	mA
Peak Repetitive Forward Current		I _{FRM}	625	mA
Non-Repetitive Peak Forward Surge Current	at t = 1 µs at t = 1 s	I _{FSM}	4 1	А
Power Dissipation		P _d	350	mW
Operating and Storage Temperature Range		T _j , T _{stg}	- 65 to + 150	°C

Characteristics at T_a = 25 °C

Parameter	Symbol	Min.	Max.	Unit
Forward Voltage at I_F = 20 mA at I_F = 100 mA at I_F = 200 mA	V _F		0.87 1 1.25	V
Reverse Current at V_R = 240 V at V_R = 240 V, T_j = 150 °C	I _R		100 100	nΑ μΑ
Reverse Breakdown Voltage at I _R = 100 μA	V _{(BR)R}	350	-	V
Total Capacitance at $V_R = 0$, $f = 1$ MHz	C _T	-	5	pF
Reverse Recovery Time at I_F = I_R = 30 mA , I_{rr} = 0.1 I_R , R_L = 100 Ω	t _{rr}	-	50	ns

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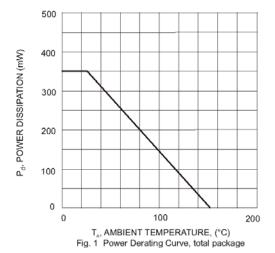


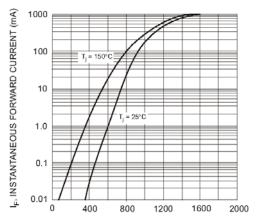




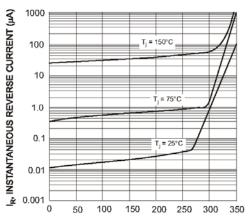


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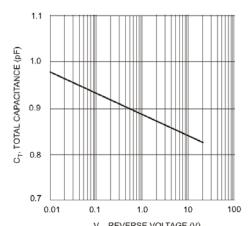




V_F, INSTANTANEOUS FORWARD VOLTAGE (mV) Fig. 2 Typical Forward Characteristics, per element



 $V_{\mbox{\tiny R}}$, INSTANTANEOUS REVERSE VOLTAGE (V) Fig. 3 Typical Reverse Characteristics, per element



V_R, REVERSE VOLTAGE (V) Fig. 4 Typical Total Capacitance vs. Reverse Voltage, per element



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Dated: 18/12/2007